



## STS1HNK60

N-CHANNEL 600V - 8Ω - 0.3A SO-8  
SuperMESH™ Power MOSFET

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>	P <sub>w</sub>
STS1HNK60	600 V	< 8.5 Ω	0.3 A	2 W

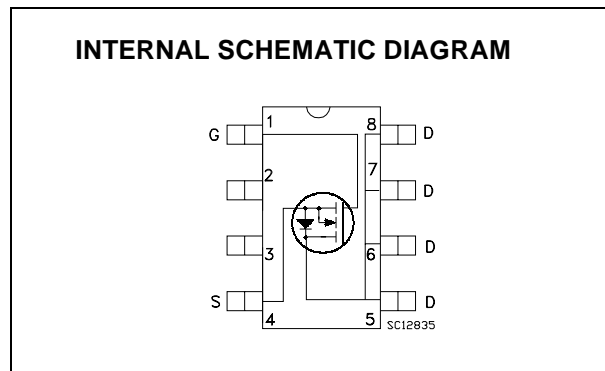
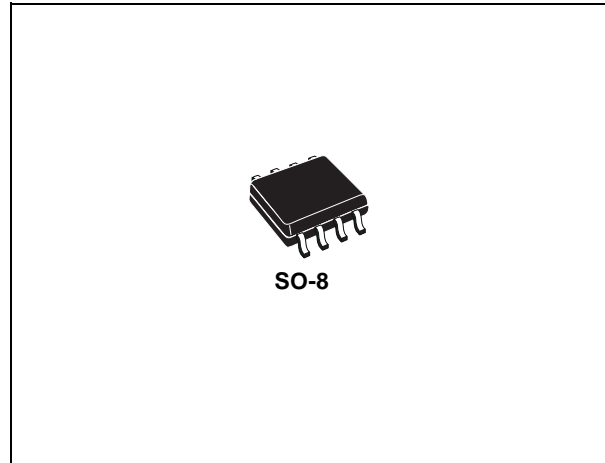
- TYPICAL R<sub>DS(on)</sub> = 8 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- GATE CHARGE MINIMIZED
- NEW HIGH VOLTAGE BENCHMARK

### DESCRIPTION

The SuperMESH™ series is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, special care is taken to ensure a very good dv/dt capability for the most demanding applications. Such series complements ST full range of high voltage MOSFETs including revolutionary MDmesh™ products.

### APPLICATIONS

- SWITCH MODE LOW POWER SUPPLIES (SMPS)
- LOW POWER, LOW COST CFL (COMPACT FLUORESCENT LAMPS)
- LOW POWER BATTERY CHARGERS



### ORDERING INFORMATION

SALES TYPE	MARKING	PACKAGE	PACKAGING
STS1HNK60	S1HNK60	SO-8	TAPE & REEL

## STS1HNK60

### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	600	V
V <sub>DGR</sub>	Drain-gate Voltage (R <sub>GS</sub> = 20 kΩ)	600	V
V <sub>GS</sub>	Gate- source Voltage	± 30	V
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 25°C	0.3	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 100°C	0.19	A
I <sub>DM</sub> (•)	Drain Current (pulsed)	1.2	A
P <sub>TOT</sub>	Total Dissipation at T <sub>C</sub> = 25°C	2	W
	Derating Factor	0.016	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	3	V/ns
T <sub>j</sub> T <sub>stg</sub>	Operating Junction Temperature Storage Temperature	-65 to 150	°C

(•) Pulse width limited by safe operating area

(1) I<sub>SD</sub> ≤ 0.3A, di/dt ≤ 100A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>j</sub> ≤ T<sub>JMAX</sub>.

### THERMAL DATA

R <sub>thj-amb</sub>	Thermal Resistance Junction-ambient Max	62.5	°C/W
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### ELECTRICAL CHARACTERISTICS (T<sub>CASE</sub> = 25°C UNLESS OTHERWISE SPECIFIED)

ON/OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 1 mA, V <sub>GS</sub> = 0	600			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating, T <sub>C</sub> = 125 °C			1 50	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 30 V			±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2.25	3	3.7	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 0.5 A		8	8.5	Ω

**ELECTRICAL CHARACTERISTICS (CONTINUED)**

**DYNAMIC**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs}$ (1)	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ , $I_D = 0.5 \text{ A}$		1		S
$C_{iss}$ $C_{oss}$ $C_{rss}$	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25\text{V}$ , $f = 1 \text{ MHz}$ , $V_{GS} = 0$		156 23.5 3.8		pF pF pF

**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$	Turn-on Delay Time Rise Time	$V_{DD} = 300 \text{ V}$ , $I_D = 0.5 \text{ A}$ $R_G = 4.7\Omega$ , $V_{GS} = 10 \text{ V}$ (Resistive Load see, Figure 3)		6.5 5		ns ns
$Q_g$ $Q_{gs}$ $Q_{gd}$	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 480 \text{ V}$ , $I_D = 1 \text{ A}$ , $V_{GS} = 10\text{V}$ , $R_G = 4.7\Omega$		7 1.1 3.4	10	nC nC nC

**SWITCHING OFF**

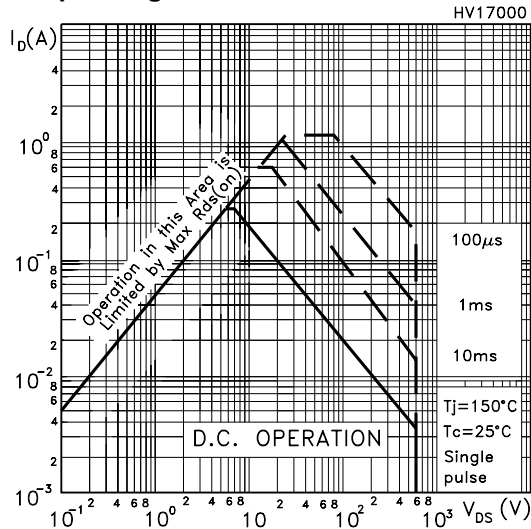
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ $t_f$	Turn-off Delay Time Fall Time	$V_{DD} = 300 \text{ V}$ , $I_D = 0.5 \text{ A}$ $R_G = 4.7\Omega$ , $V_{GS} = 10 \text{ V}$ (Resistive Load see, Figure 3)		19 25		ns ns
$t_{r(voff)}$ $t_f$ $t_c$	Off-voltage Rise Time Fall Time Cross-over Time	$V_{DD} = 480\text{V}$ , $I_D = 1.0 \text{ A}$ , $R_G = 4.7\Omega$ , $V_{GS} = 10\text{V}$ (Inductive Load see, Figure 5)		24 25 44		ns ns ns

**SOURCE DRAIN DIODE**

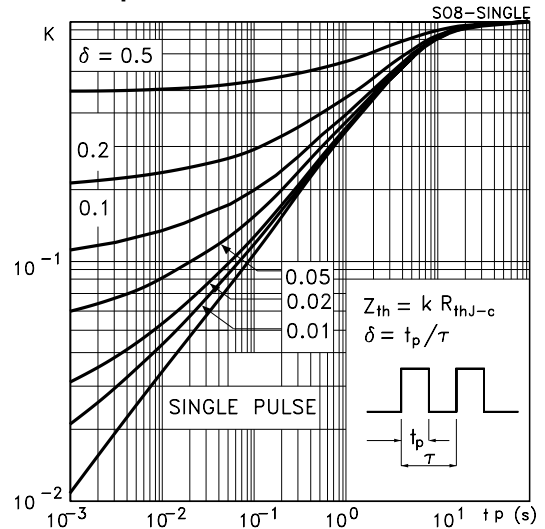
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$ $I_{SDM}$ (2)	Source-drain Current Source-drain Current (pulsed)				0.3 1.2	A A
$V_{SD}$ (1)	Forward On Voltage	$I_{SD} = 0.3 \text{ A}$ , $V_{GS} = 0$			1.6	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 0.3 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 25 \text{ V}$ , $T_j = 150^\circ\text{C}$ (see test circuit, Figure 5)		229 377 3.3		ns $\mu\text{C}$ A

Note: 1. Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %.  
2. Pulse width limited by safe operating area.

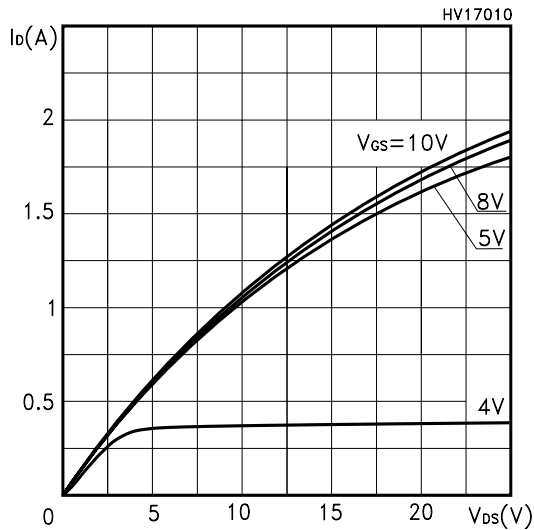
Safe Operating Area



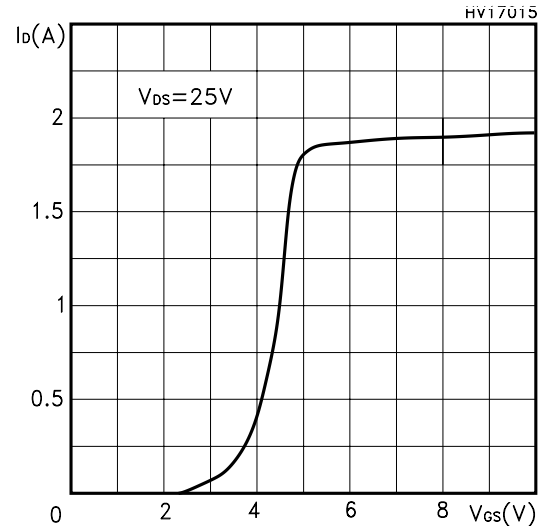
Thermal Impedance



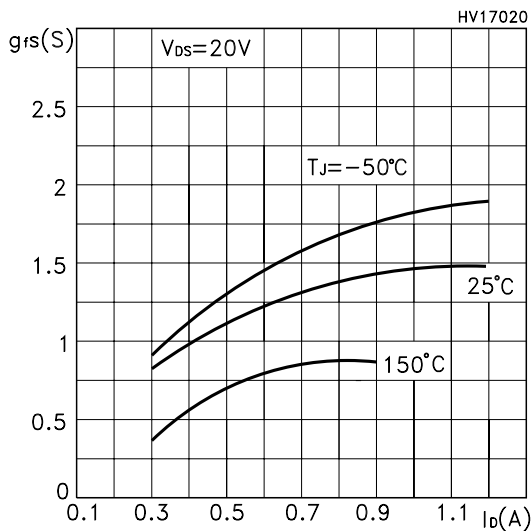
Output Characteristics



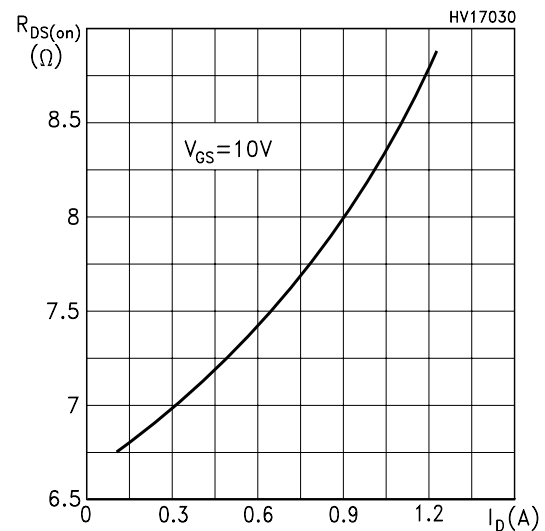
Transfer Characteristics



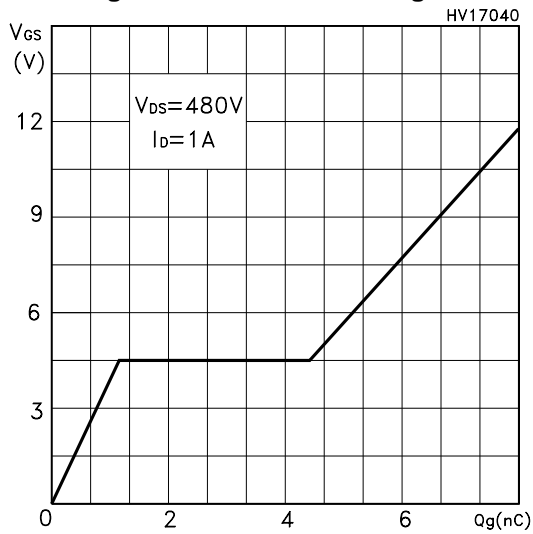
Transconductance



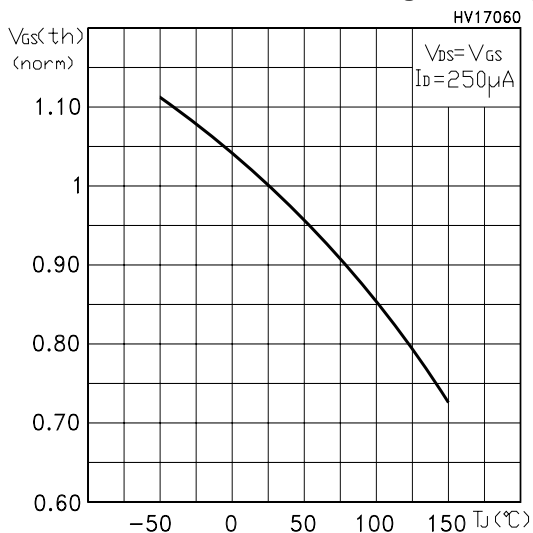
Static Drain-source On Resistance



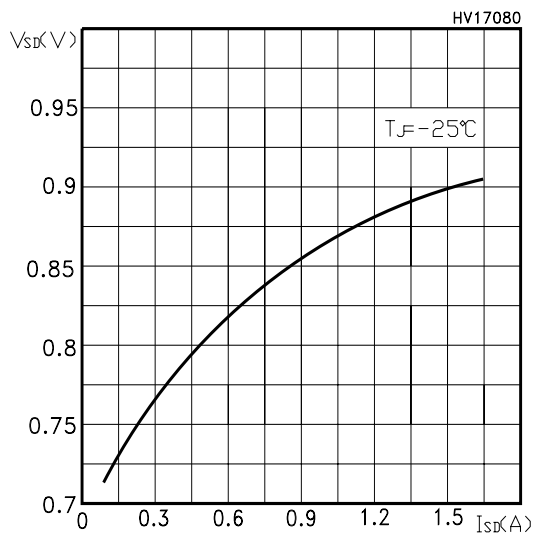
**Gate Charge vs Gate-source Voltage**



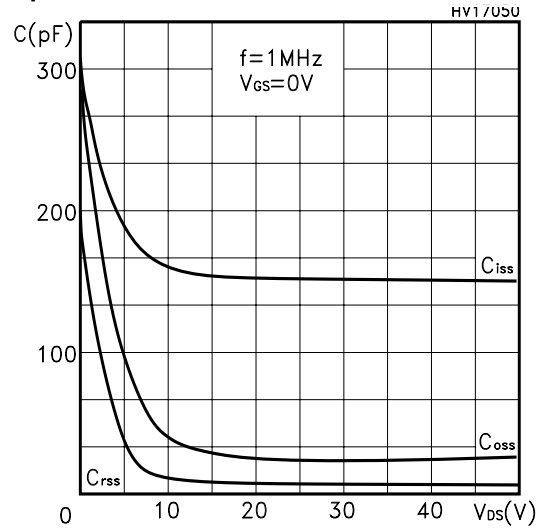
**Normalized Gate Threshold Voltage vs Temp.**



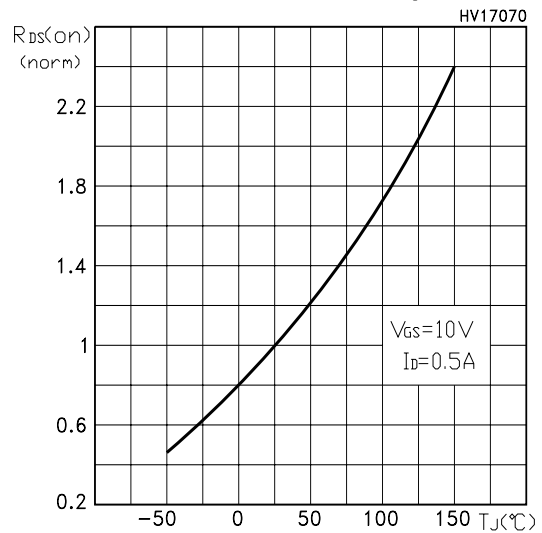
**Source-drain Diode Forward Characteristics**



**Capacitance Variations**



**Normalized On Resistance vs Temperature**



**Normalized BVDSS vs Temperature**

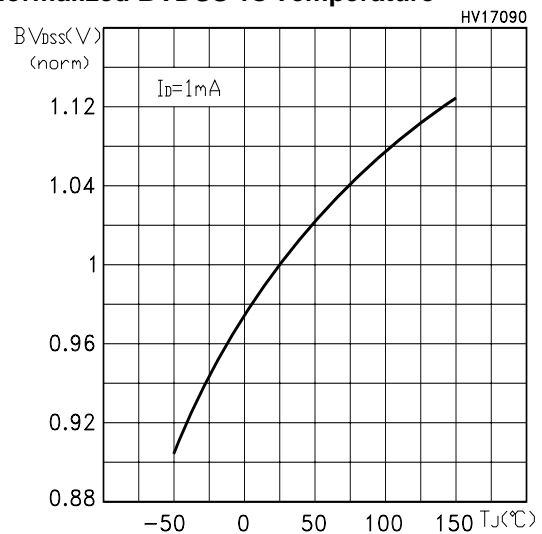


Fig. 1: Unclamped Inductive Load Test Circuit

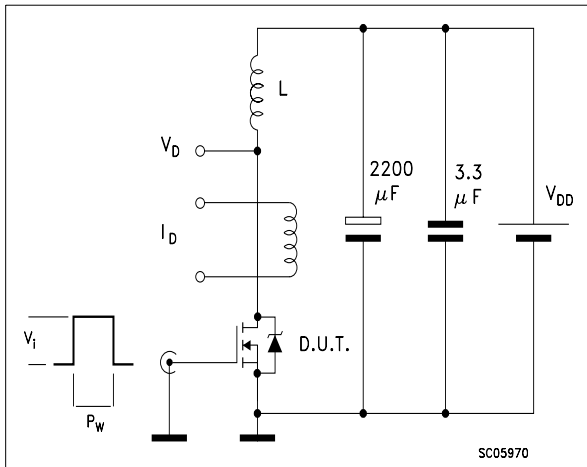


Fig. 2: Unclamped Inductive Waveform

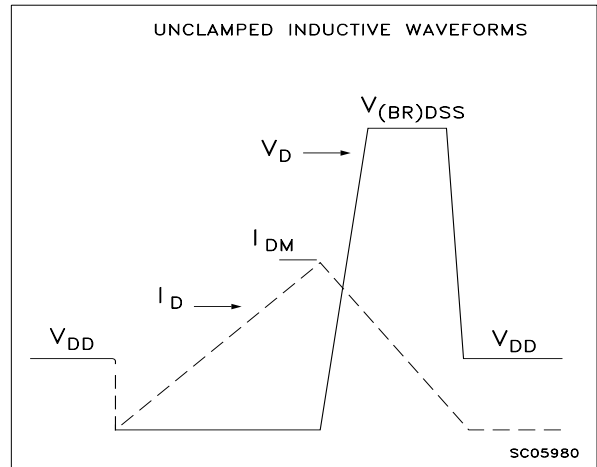


Fig. 3: Switching Times Test Circuit For Resistive Load

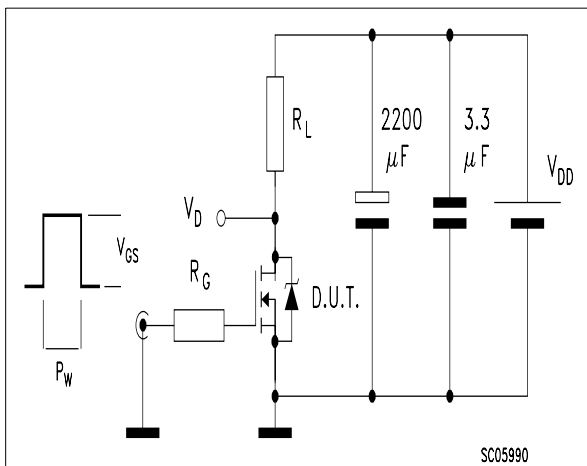


Fig. 4: Gate Charge test Circuit

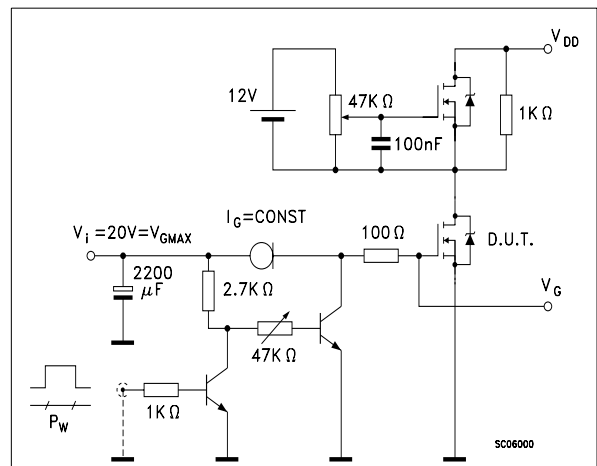
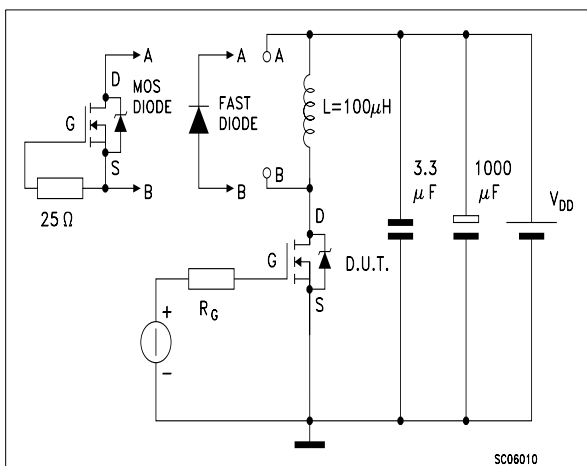
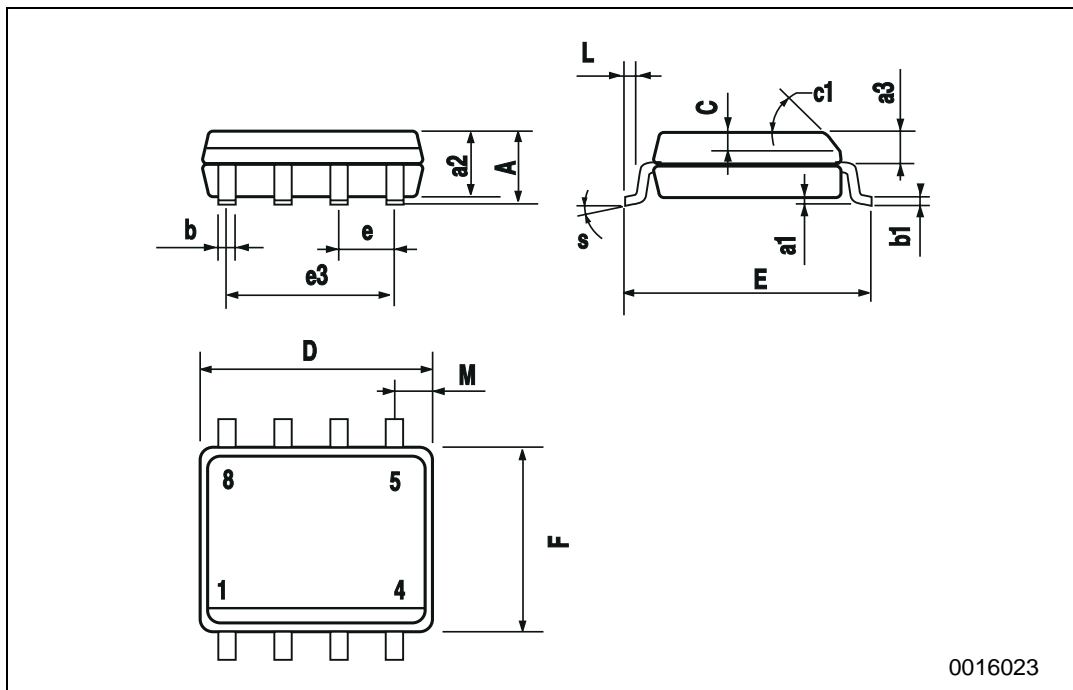


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



SO-8 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.25	0.003		0.009
a2			1.65			0.064
a3	0.65		0.85	0.025		0.033
b	0.35		0.48	0.013		0.018
b1	0.19		0.25	0.007		0.010
C	0.25		0.5	0.010		0.019
c1	45 (typ.)					
D	4.8		5.0	0.188		0.196
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.14		0.157
L	0.4		1.27	0.015		0.050
M			0.6			0.023
S	8 (max.)					



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